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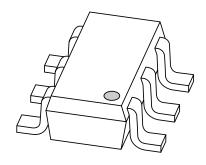
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PIMT1 PNP general purpose double transistor

Product data sheet 2001 Oct 22



PNP general purpose double transistor

PIMT1

FEATURES

- 600 mW total power dissipation
- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and required PCB area
- · Reduced pick and place costs.

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

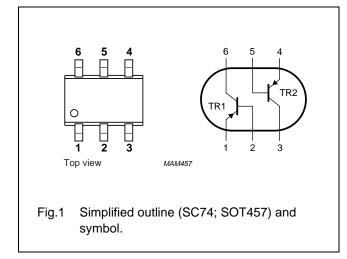
PNP transistor pair in an SC-74 (SOT457) plastic package.

MARKING

TYPE NUMBER	MARKING CODE		
PIMT1	M1		

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	_	-40	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		-	-200	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	.	<u> </u>	•	•	•
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	600	mW

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

PNP general purpose double transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	208	K/W

Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	stor				
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	-100	nA
		$V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	-10	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_C = 0$	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -6 \text{ V}; I_{C} = -1 \text{ mA}$	120	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -50 \text{ mA}$; $I_B = -5 \text{ mA}$; note 1	_	-200	mV
C _c	collector capacitance	$V_{CB} = -12 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	2.2	pF
f _T	transition frequency	$V_{CE} = -12 \text{ V}; I_{C} = -2 \text{ mA};$ f = 100 MHz	100	_	MHz

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

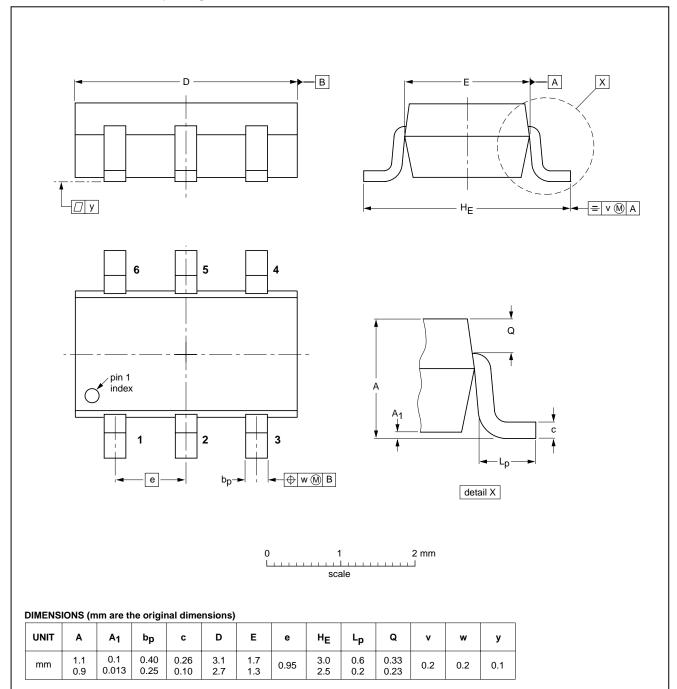
PNP general purpose double transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT457			SC-74			-97-02-28 01-05-04

PNP general purpose double transistor

PIMT1

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

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Contact information

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